

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型 名	社 名	用 途	構 造	最大 定 格 ($T_a=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a=25^{\circ}\text{C}$)										外 形	備 考
				V_{CBO} (V)	V_{CEO} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値 (μA) V_{CB} (V)		直流又はパルス h_{FE} I_C (mA)		バイアス V_{CB} (V) I_C (mA)		h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)		
1	2	3	4	5					6		7		8		9		10	11	12	

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ: COMPLEMENTARY TO

型 名	社 名	用 途	構 造	最 大 定 格 ($T_a = 25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a = 25^{\circ}\text{C}$)													外 形	備 考
				V_{CE0} (V)	V_{E0} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値 (μA)	V_{CB} (V)	直 流 又 は パ ル ス h_{FE}			バ イ ア ス		h_{fe}	h_{ie} h_{ib}^* (Ω)	h_{re} h_{rb}^* ($\times 10^{-4}$)	h_{oe} h_{ob}^* (μU)	$f_{\beta T}^*$ (Mc)	C_{ob} (pF)		
2SD296	オリジン	PA. SW	Si. T	800	10	30 A	200 W ($T_c=25^{\circ}\text{C}$)	150	5 mA	800	40	5	10 A	12	-2.5 A				$f_{\beta T}$ 150kHz			154	
" 297	日電	"	Si. EM _e	150	7	3 A	25 W ($T_c=25^{\circ}\text{C}$)	150	500	80	70	2	2 A	10	-100				10 *			134	
" 298																							
" 299	松下	PA. SW	Si. Me	1500	5	5 A	16 W ($T_c=90^{\circ}\text{C}$)	115	1mA	1500	> 2	5	4 A			$V_{CE(\text{sat})} < 10\text{V}$, $V_{BE(\text{sat})} < 1.6\text{V}$ (4.5 A, 2 A)						102	
" 300	"	"	"	1500	5	5 A	16 W ($T_c=90^{\circ}\text{C}$)	115	1mA	1500	> 3	10	2.5 A			$V_{CE(\text{sat})} < 10\text{V}$, $V_{BE(\text{sat})} < 1.6\text{V}$ (2.5 A, 0.85 A)						102	水平偏向用
" 301	富士通	SW	Si. DJ	80	6	10 A	50 W ($T_c=25^{\circ}\text{C}$)	175	30	30	2500	4	5 A			$t_d < 11\mu\text{S}$, $t_r < 53\mu\text{S}$, $t_{sig} < 16\mu\text{S}$						102	ダーリントン 接 続
" 302																							
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" 306																							
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" 308																							
" 309																							
★ " 310	オリジン	PA. SW	Si. T	800	10	15 A	150 W ($T_c=25^{\circ}\text{C}$)	150	3mA	800	20	5	7.5 A	12	-2 A				$f_{\beta T}$ 150kHz			102	
★ " 311	"	"	"	800	10	15 A	150 W ($T_c=25^{\circ}\text{C}$)	150	3mA	800	40	5	7.5 A	12	-2 A				$f_{\beta T}$ 150kHz			102	
★ " 312	松下	PA	Si. TM _e	800	6	500	25 W ($T_c=100^{\circ}\text{C}$)	150	1 mA	800	60	10	600	10	-100				5 *			102	
★ " 313	三洋	"	Si. T	60	5	3 A	30 W ($T_c=25^{\circ}\text{C}$)	150	100	20	40-320	2	1 A	5	-500				8 *	65		268	
★ " 314	"	"	"	60	5	3 A	30 W ($T_c=25^{\circ}\text{C}$)	150	100	20	40-320	2	1 A	5	-500				8 *	65		267	
" 315	"	"	"	60	5	4 A	35 W ($T_c=25^{\circ}\text{C}$)	150	100	20	40-320	2	1 A	5	-500				8 *			99	2SB509 とコンパリ
★ " 316	ソニー	"	Si. TM _e	80	5	7 A	80 W ($T_c=25^{\circ}\text{C}$)	150	100	50	70	2	3 A	10	-500				12 *	260		102	
★ " 317	松下	PA	Si. T	60	8	3 A	25 W ($T_c=25^{\circ}\text{C}$)	150	30	20	60	3	1 A	10	-200				$f_{\beta T} =$ 25 kHz			268	
★ " 318	"	"	"	60	8	3 A	25 W ($T_c=25^{\circ}\text{C}$)	150	30	20	60	3	1 A	10	-200				$f_{\beta T} =$ 25 kHz			267	
★ " 319	"	"	Si. DJ	110	7	10 A	100 W ($T_c=25^{\circ}\text{C}$)	150	30	40	35	4	5 A	10	-500				1 *			102	
★ " 320	三洋	PA. SW	Si. T	300	6	2 A	50 W ($T_c=25^{\circ}\text{C}$)	150	100	100		15	1 A										
★ " 321	松下	"	Si. TM _e	250	6	6 A	60 W ($T_c=75^{\circ}\text{C}$)	150	2 mA	250	40	5	5 A			$t_f < 1\mu\text{S}$						102	
★ " 322	日電	PA	"	120	7	7 A	80 W ($T_c=25^{\circ}\text{C}$)	150	300	120	60	5	4 A									102	
★ " 323	"	"	"	150	7	7 A	80 W ($T_c=25^{\circ}\text{C}$)	150	300	150	60	5	4 A									102	
★ " 324	松下	"	"	300	3	100	10 W ($T_c=70^{\circ}\text{C}$)	150	100	300	80	10	50									153	
★ " 325	三洋	"	Si. T	35	5	1.5 A	10 W ($T_c=25^{\circ}\text{C}$)	150	100	20	40-320	2	1 A	5	-500				8 *			268	2SB511 とコンパリ